

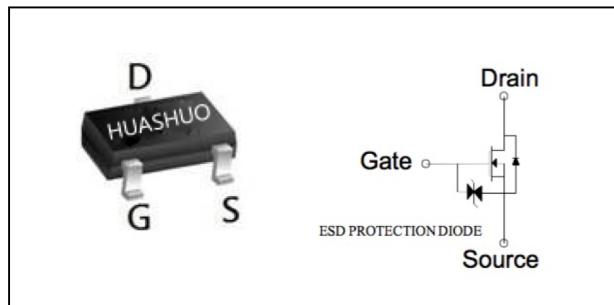
Description

We declare that the material of product compliance with RoHS requirements and Halogen Free.
 ESD protected
 Low RDS(on)

Product Summary

V _{DS}	60	V
R _{DS(ON),max}	2	Ω
I _D	0.3	A

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	300	mA
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	190	mA
I _{DM}	Pulsed Drain Current ²	1	A
P _D @T _A =25°C	Total Power Dissipation ³	0.35	W
T _{STG}	Storage Temperature Range	-40 to 150	°C
T _J	Operating Junction Temperature Range	-40 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	350	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	60	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.054	---	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}$, $I_D=200\text{mA}$	---	---	2	Ω
		$V_{\text{GS}}=4.5\text{V}$, $I_D=100\text{mA}$	---	---	3	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	1.2	---	2.5	V
$\Delta V_{\text{GS}(\text{th})}$	$V_{\text{GS}(\text{th})}$ Temperature Coefficient		---	-4.96	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{\text{DS}}=48\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 16\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 30	μA
g_{fs}	Forward Transconductance	$V_{\text{DS}}=50\text{V}$, $I_D=200\text{mA}$	---	0.18	---	S
Q_g	Total Gate Charge (4.5V)	$V_{\text{DS}}=0.5\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=200\text{mA}$	---	1.0	---	nC
Q_{gs}	Gate-Source Charge		---	0.4	---	
Q_{gd}	Gate-Drain Charge		---	1	---	
$T_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}}=30\text{V}$, $V_{\text{GEN}}=10\text{V}$, $R_G=25\Omega$, $I_D=500\text{mA}$, $RL=60\Omega$,	---	2.7	---	ns
T_r	Rise Time		---	2.5	---	
$T_{\text{d}(\text{off})}$	Turn-Off Delay Time		---	13	---	
T_f	Fall Time		---	8	---	
C_{iss}	Input Capacitance	$V_{\text{DS}}=25\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	38	---	pF
C_{oss}	Output Capacitance		---	5	---	
C_{rss}	Reverse Transfer Capacitance		---	2	---	

Diode Characteristics

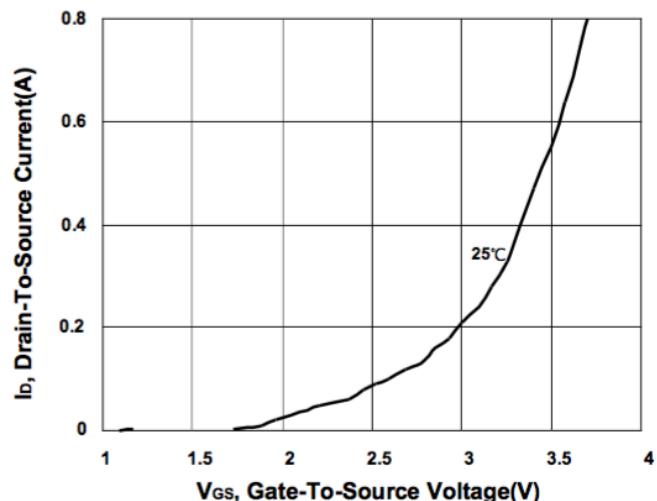
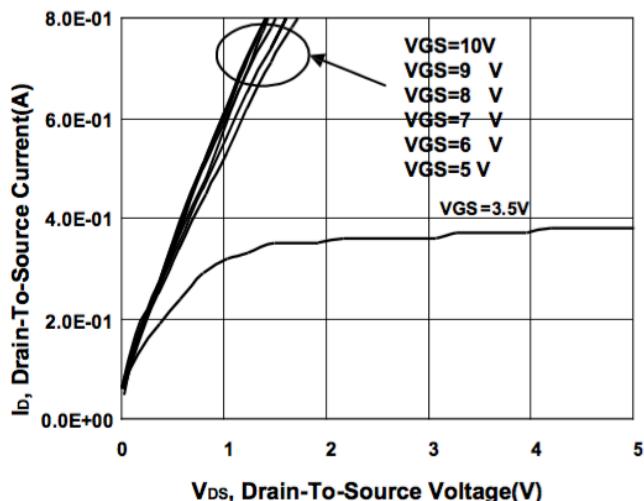
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	300	mA
I_{SM}	Pulsed Source Current ^{2,4}		---	---	1	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_s=0.5\text{A}$, $T_J=25^\circ\text{C}$	---	---	0.85	V

Note :

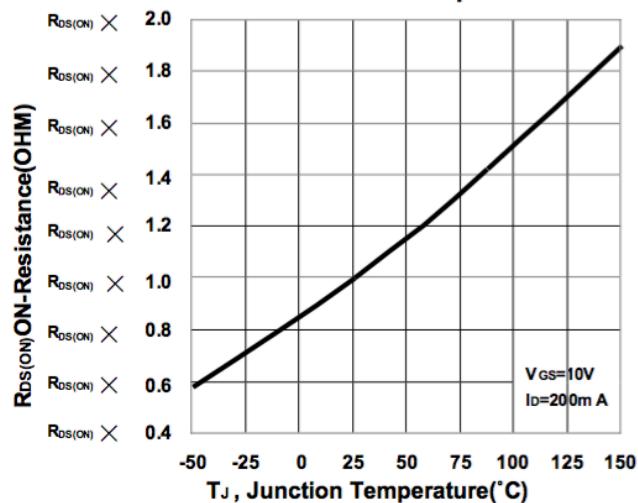
- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature.
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



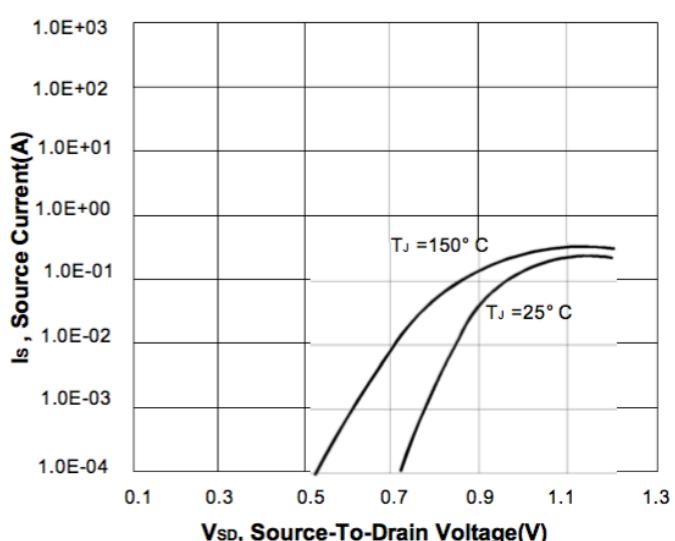
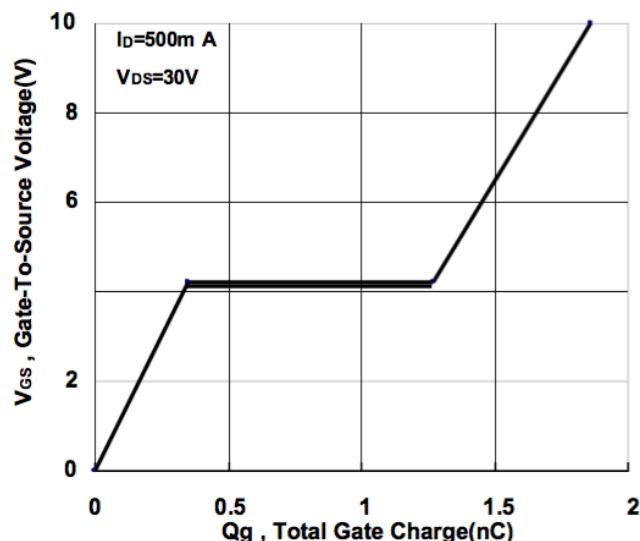
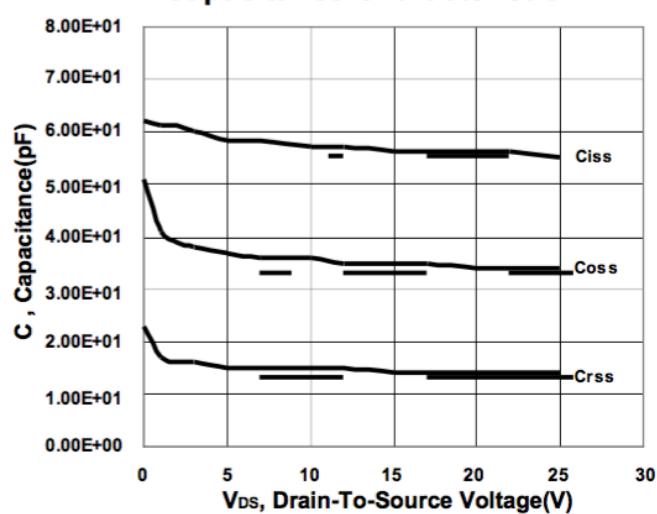
Typical Characteristics



On-Resistance VS Temperature



Capacitance Characteristic

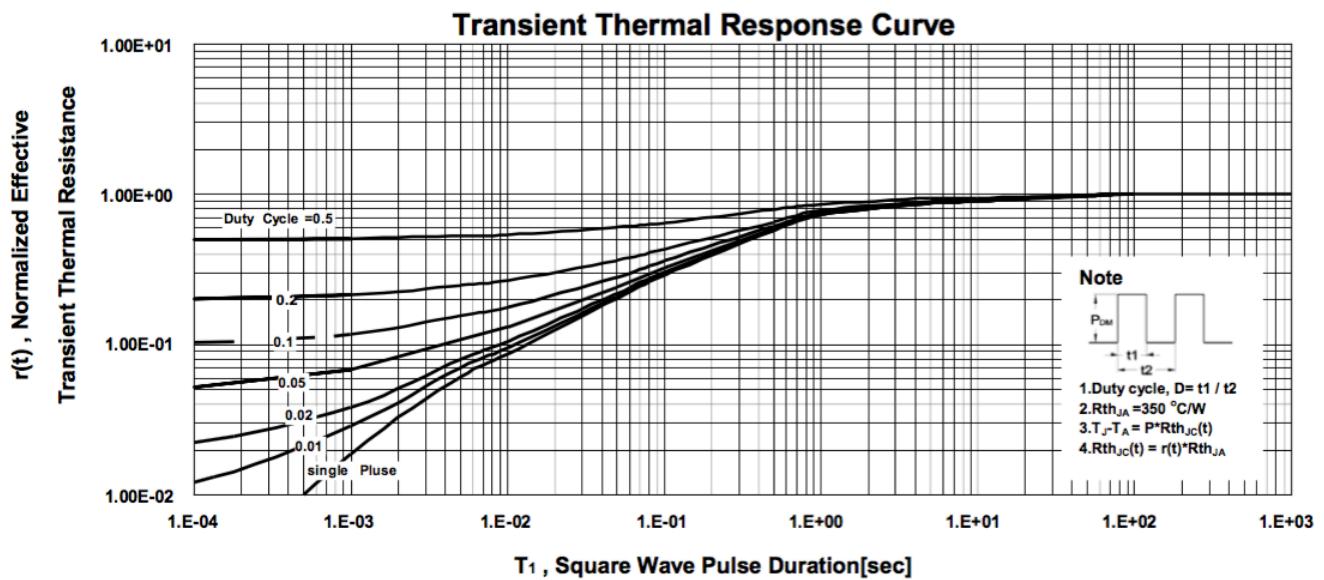
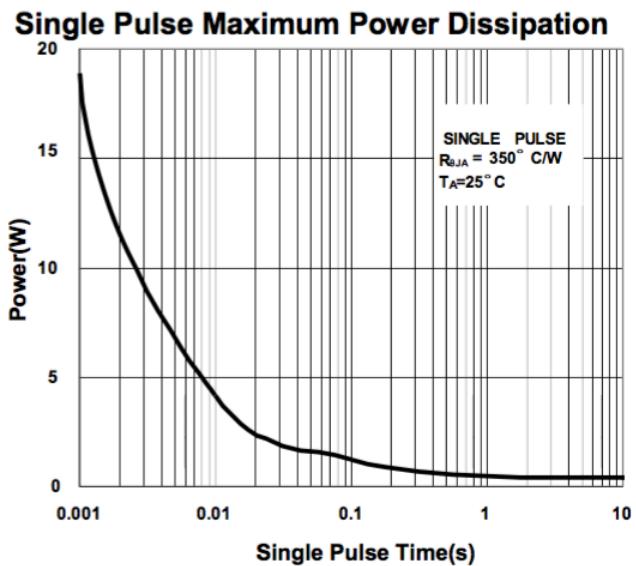
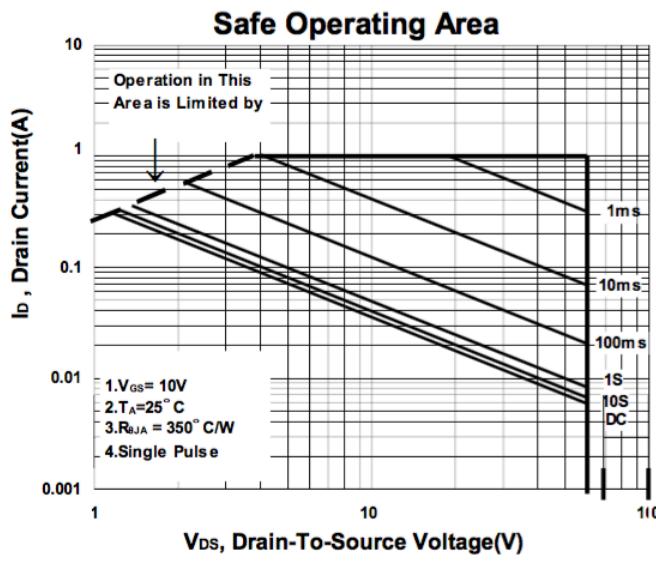




HUASHUO
SEMICONDUCTOR

HSS2N7002K

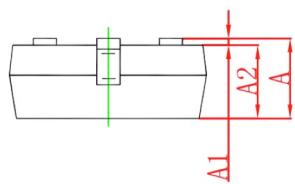
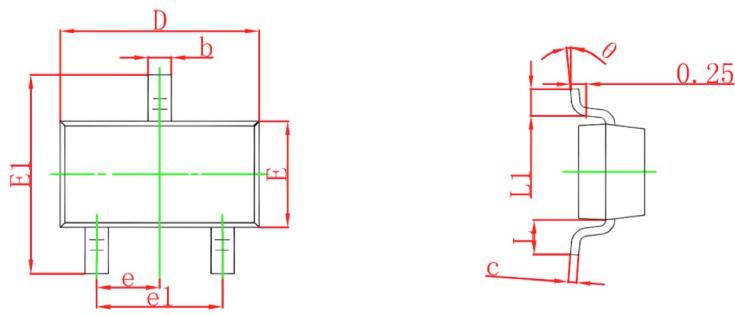
N-Ch 60V Fast Switching MOSFETs





Ordering Information

Part Number	Package code	Packaging
HSS2N7002K	SOT-23	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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